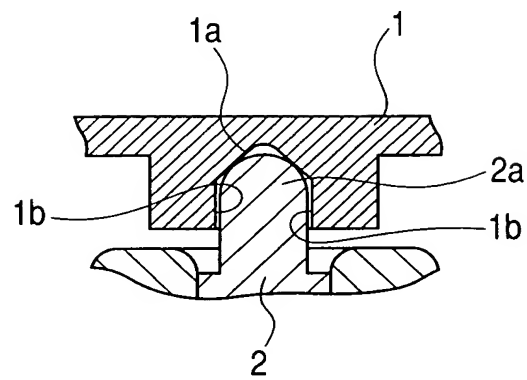


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**FIG. 1B**

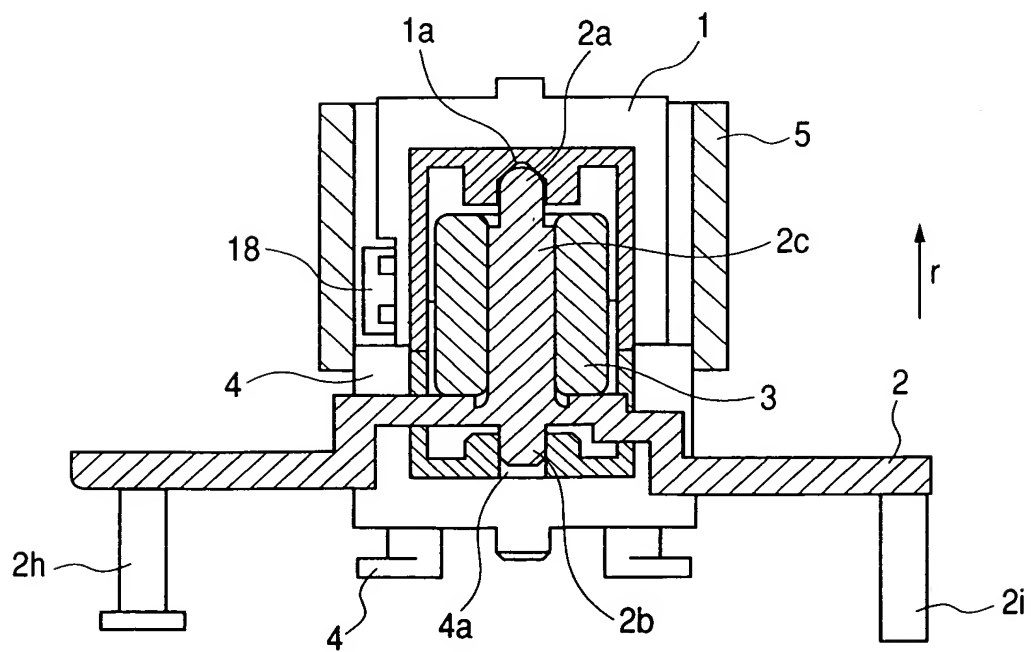


FIG. 2A

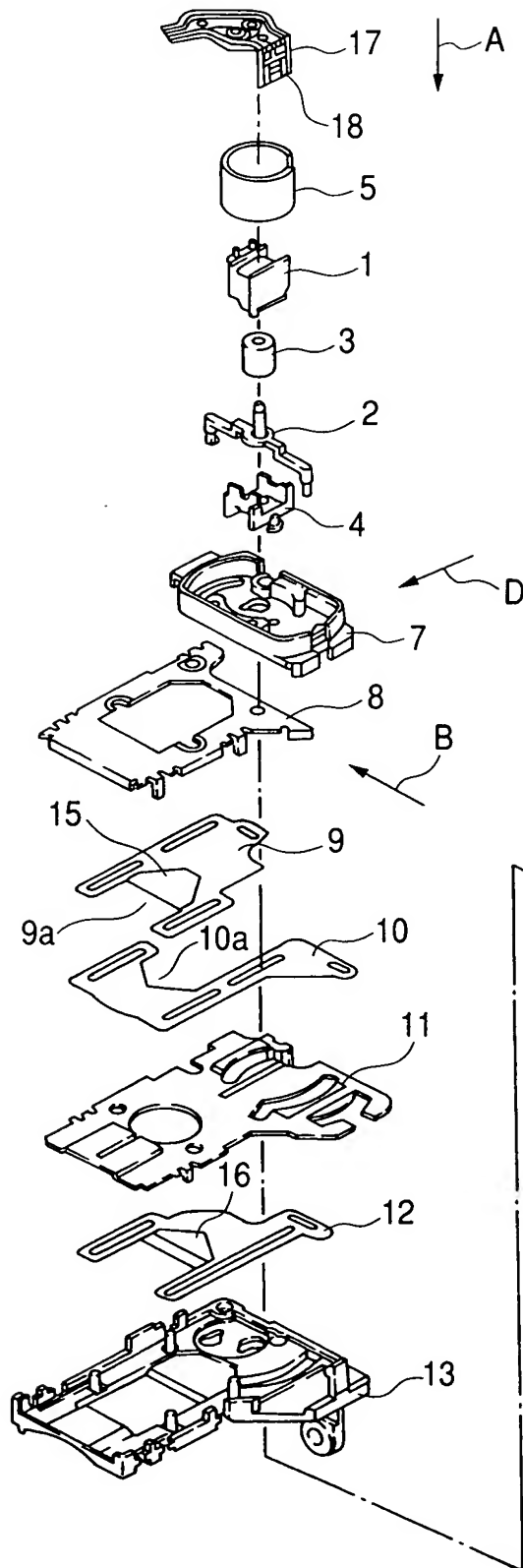


FIG. 2B

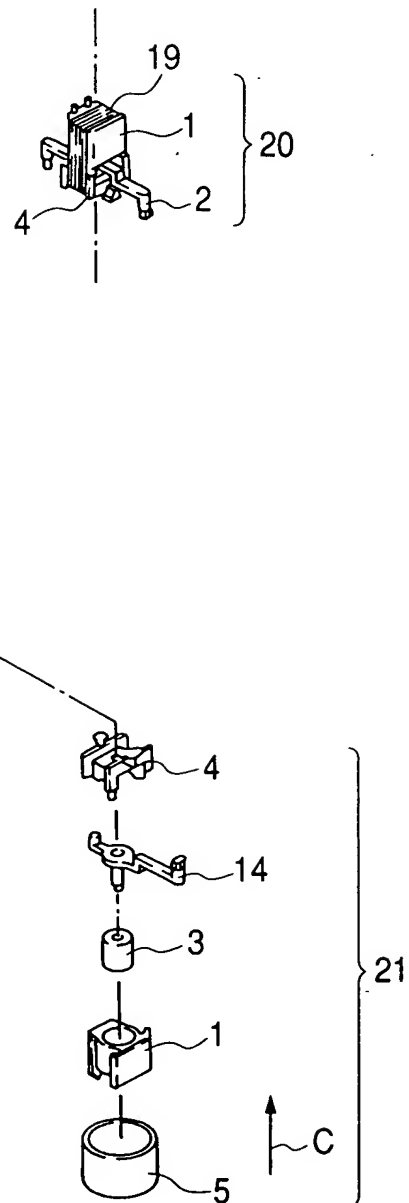


FIG. 3A

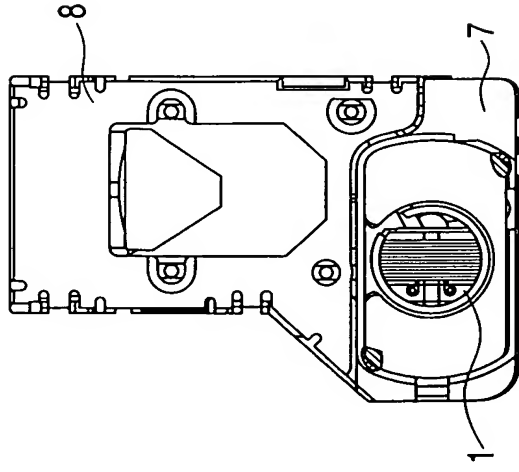


FIG. 3B

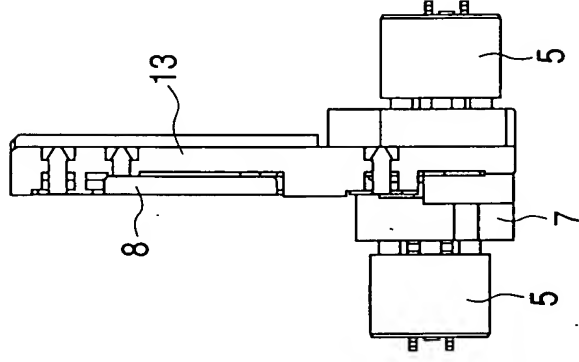


FIG. 3C

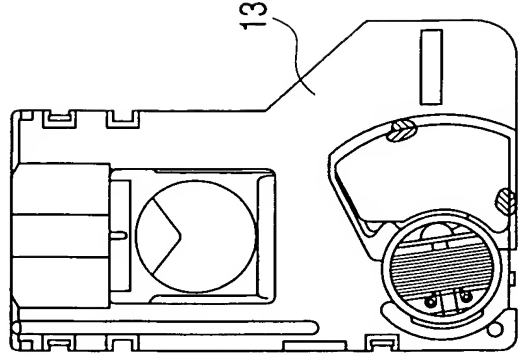
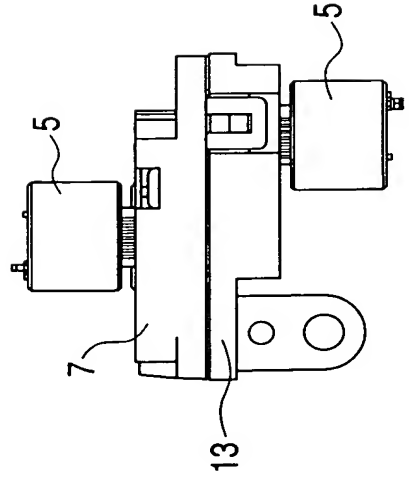
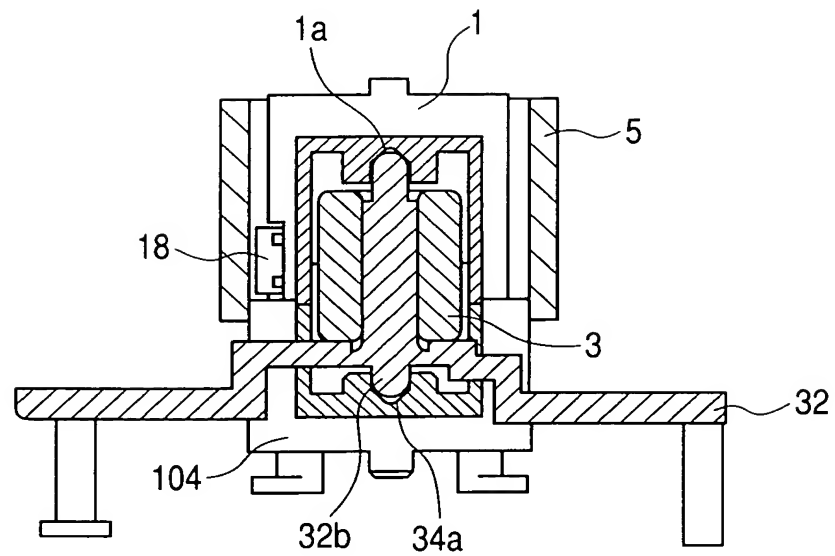


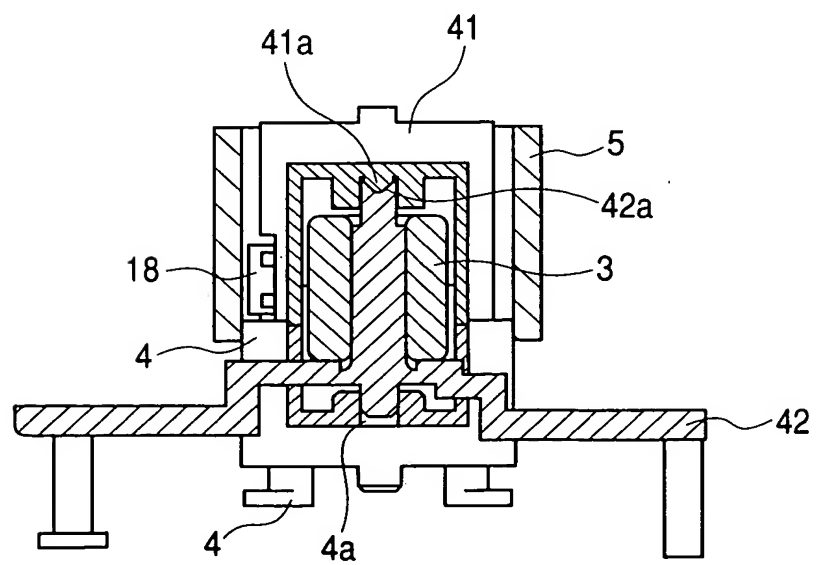
FIG. 3D



**FIG. 4**



**FIG. 5**



A cross-sectional view of a semiconductor device. A substrate 101 is shown with a trench 101a. A gate 102a is formed on the side wall of the trench 101a. A gate 102 is formed on the bottom of the trench 101a.

A detailed cross-sectional view of a semiconductor device. The central core (101) is surrounded by a ring (103) and a base (104). The top layer (102a) and bottom layer (102b) are shown. A vertical arrow 'r' indicates a radial direction. Other labels include 101a, 102c, 105, 118, 102h, 102i, and 104a.

*FIG. 7*  
*PRIOR ART*

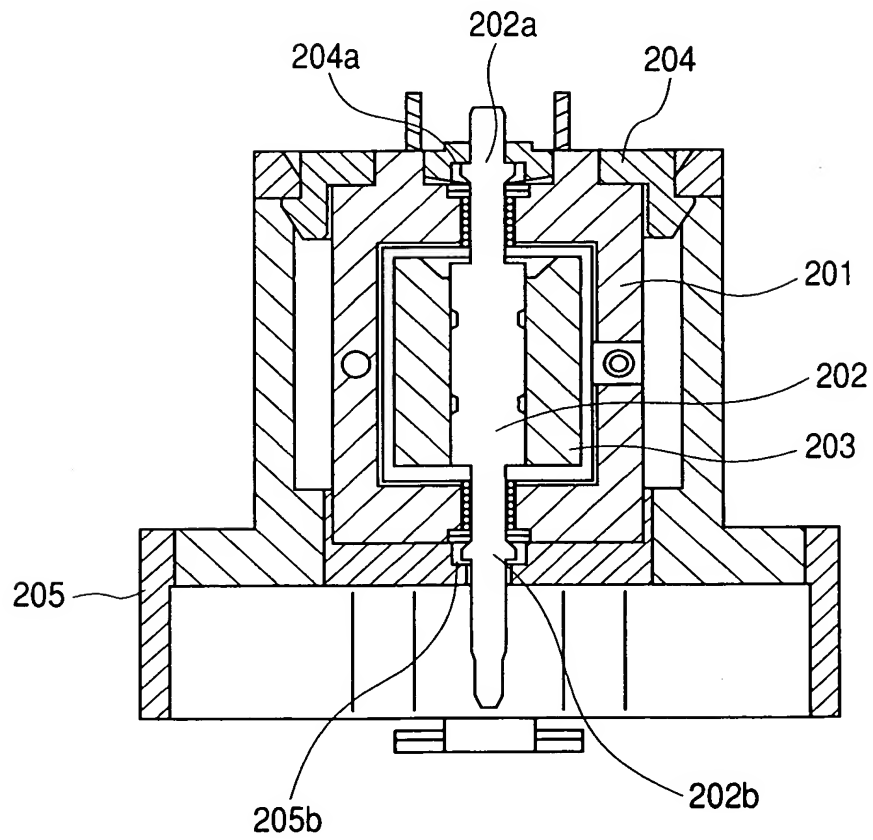


FIG. 8A

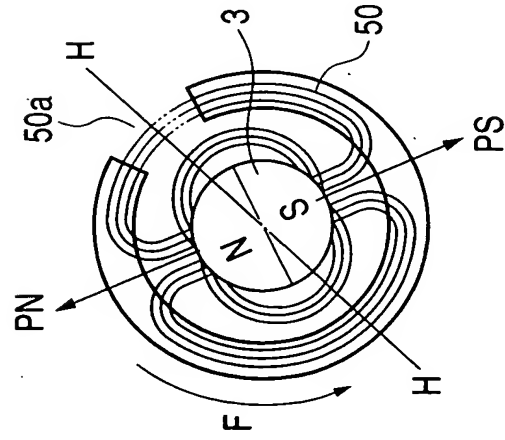


FIG. 8B

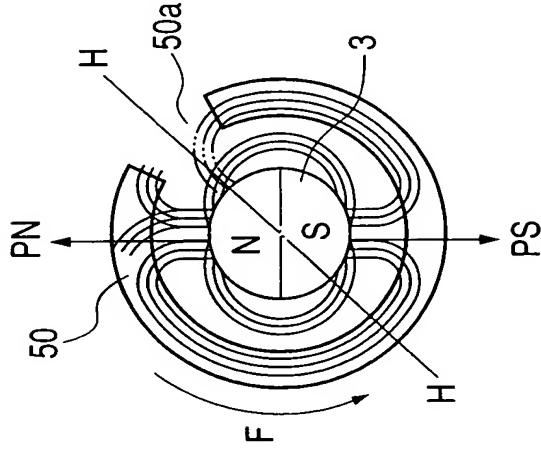


FIG. 8C

